

40V N-Channel Power SpeedFET
• General Description

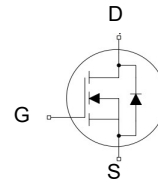
It combines advanced trench MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$.

• Features

- AEC-Q101 Qualified
- Low $R_{DS(ON)}$ to minimize conductive loss
- Low Gate Charge for fast switching
- Low Thermal resistance

• Application

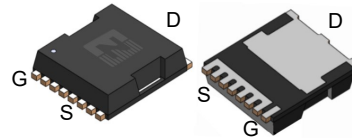
- BLDC Motor driver
- DC-DC
- Load Switch

• Product Summary


$$V_{DS} = 40V$$

$$R_{DS(ON)} = 0.52m\Omega$$

$$I_D = 390A$$



TOLL


• Ordering Information:

Part NO.	ZMSA005N04HR
Marking	ZMS005N04H
Packing Information	REEL TAPE
Basic ordering unit (pcs)	2000

• Absolute Maximum Ratings ($T_C=25^{\circ}C$)

Parameter	Symbol	Conditions	Value	Unit
Drain-Source Voltage	V_{DS}		40	V
Gate-Source Voltage ^①	V_{GS}		± 20	V
Continuous Drain Current	I_D	$T_C=25^{\circ}C$	390	A
	I_D	$T_C=75^{\circ}C$	390	A
	I_D	$T_C=100^{\circ}C$	345	A
Pulsed Drain Current	I_{DM}	Pulsed; $t_p \leq 10 \mu s$; $T_{mb} = 25^{\circ}C$;	1560	A
Total Power Dissipation	P_D	$T_C=25^{\circ}C$	375	W
Total Power Dissipation	P_D	$T_A=25^{\circ}C$	4.2	W
Operating Junction Temperature	T_J		-55 to +175	$^{\circ}C$
Storage Temperature	T_{STG}		-55 to +175	$^{\circ}C$
Single Pulse Avalanche Energy	E_{AS}	$L=0.1mH$, $V_{GS}=10V$, $R_g=25\Omega$,	756	mJ
		$L=0.3mH$, $V_{GS}=10V$, $R_g=25\Omega$,	1210	mJ
ESD Level (HBM)	CLASS 2			

•Thermal resistance

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal resistance, junction - case	R_{thJC}		-	0.4	°C/W
Thermal resistance, junction-ambient	$R_{thJA}^{②}$		-	36	°C/W
Soldering temperature	T_{sold}		-	260	°C

•Electronic Characteristics

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	40			V
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS}=V_{DS}, I_D=250\mu A$	2	2.7	4	V
Drain-Source Leakage Current	I_{DSS}	$V_{GS}=0V, V_{DS}=40V$			1.0	μA
Gate- Source Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$			100	nA
Static Drain-source On Resistance	$R_{DS(ON)}$	$V_{GS}=10V, I_D=40A$		0.52	0.65	m Ω
Forward Transconductance	g_{FS}	$V_{DS}=5V, I_{SD}=10A$		30		S
Diode Forward Voltage	V_{FSD}	$V_{GS}=0V, I_{SD}=40A$			1.3	V

•Dynamic characteristics

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Input capacitance	C_{iss}	$f=1MHz, V_{DS}=25V$	-	10620	-	pF
Output capacitance	C_{oss}		-	2810	-	
Reverse transfer capacitance	C_{rss}		-	115	-	
Gate Resistance	R_g	$f=1MHz$	-	1.6		Ω
Total gate charge	Q_g	$V_{DD}=15V, I_D=20A, V_{GS}=10V$	-	155	-	nC
Gate - Source charge	Q_{gs}		-	35	-	
Gate - Drain charge	Q_{gd}		-	32	-	
Turn-ON Delay time	$t_{D(on)}$	$V_{GS}=10V, V_{DS}=15V, R_G=3.3\Omega, I_D=20A$	-	65	-	ns
Turn-ON Rise time	t_r		-	31	-	ns
Turn-Off Delay time	$t_{D(off)}$		-	85	-	ns
Turn-Off Fall time	t_f		-	78	-	ns
Reverse Recovery Time	t_{RR}	$V_{DD}=20V, dI_S/dt=100A/\mu s, I_S=50A$	-	97	-	ns
Reverse Recovery Charge	Q_{RR}		-	135	-	nC

Fig.1 Gate-Charge Characteristics

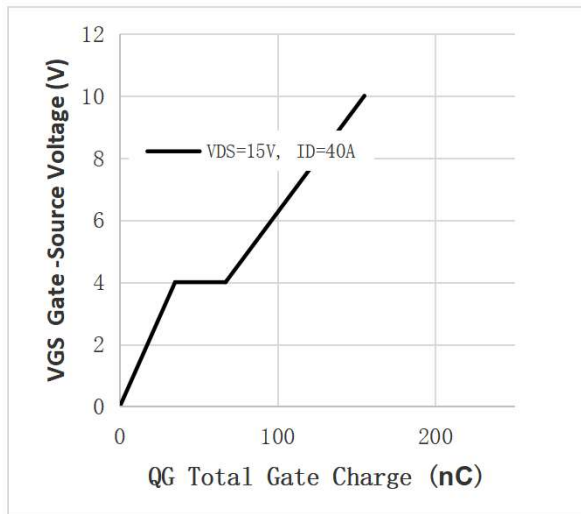


Fig.2 Capacitance Characteristics

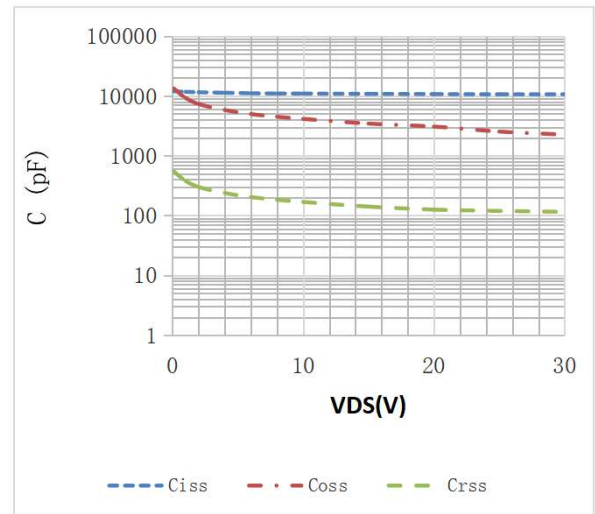


Fig.3 Power Dissipation

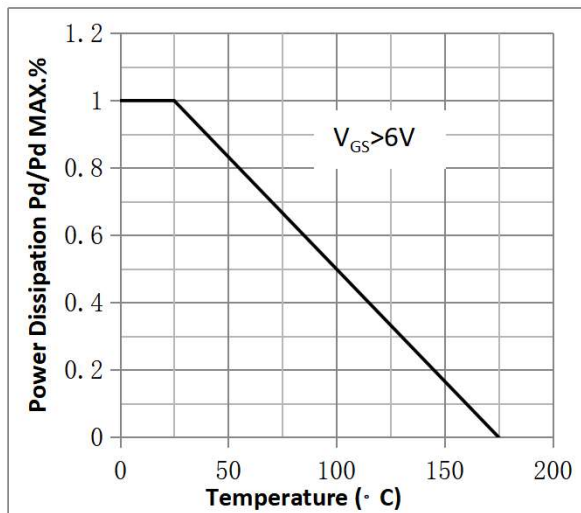


Fig.4 Typical output Characteristics

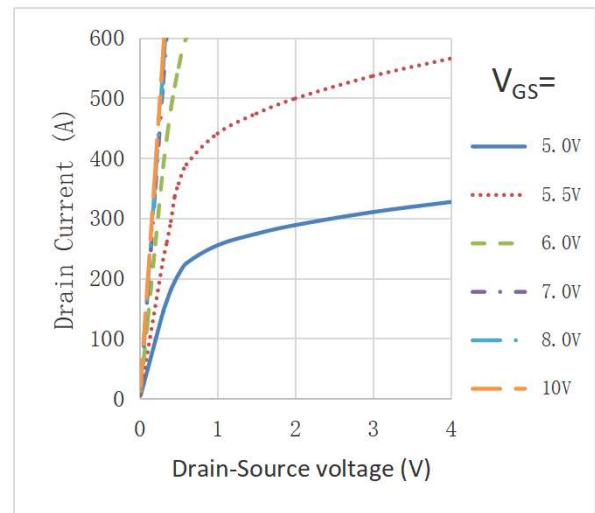


Fig.5 Threshold Voltage V.S Junction Temperature

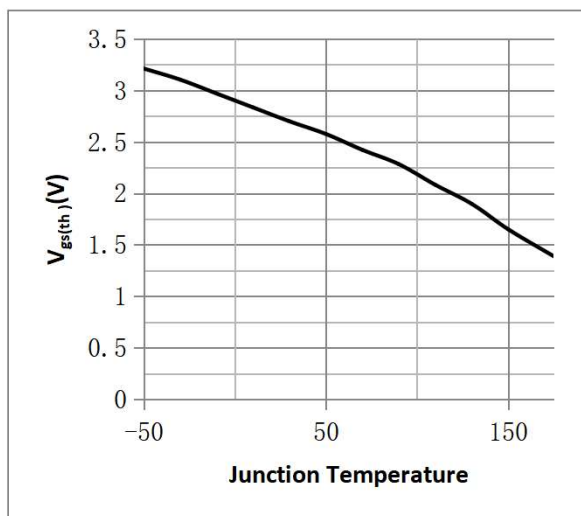


Fig.6 Resistance V.S Drain Current

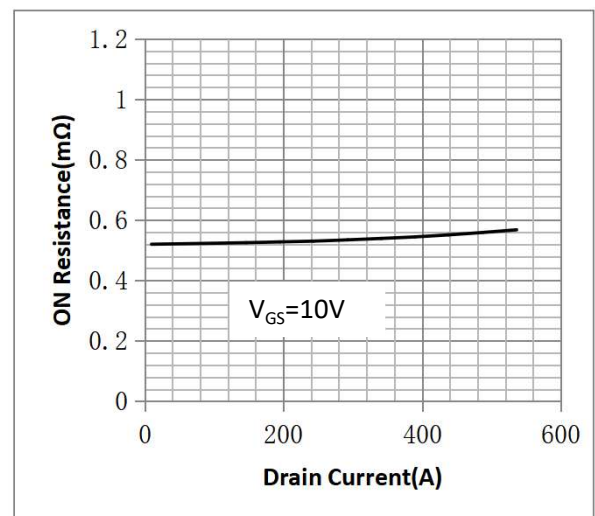


Fig.7 On-Resistance VS Gate Source Voltage

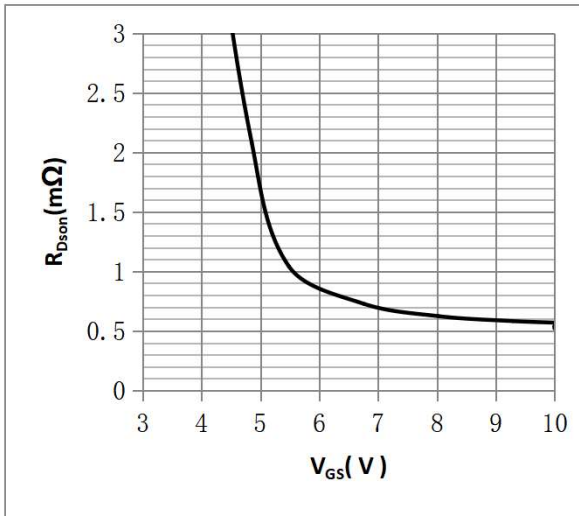


Fig.8 On-Resistance V.S Junction Temperature

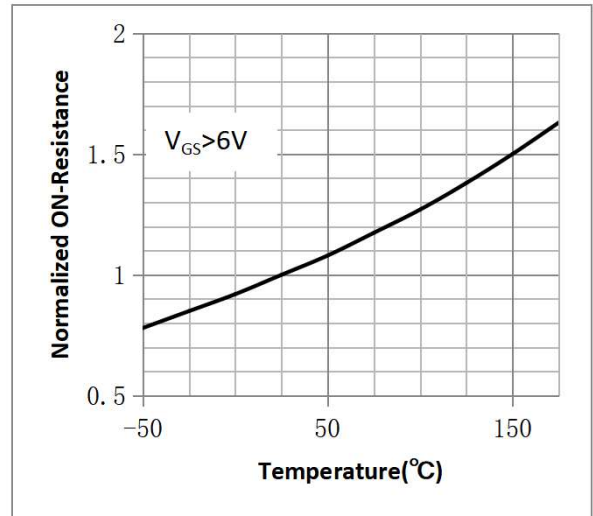


Figure 9. Diode Forward Voltage vs. Current

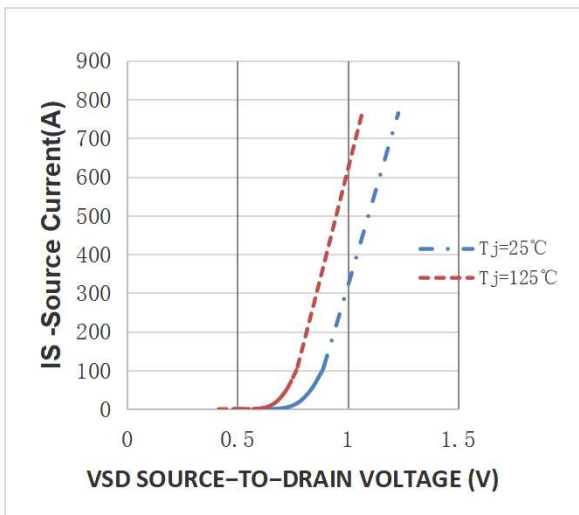


Figure 10. Transfer Characteristics

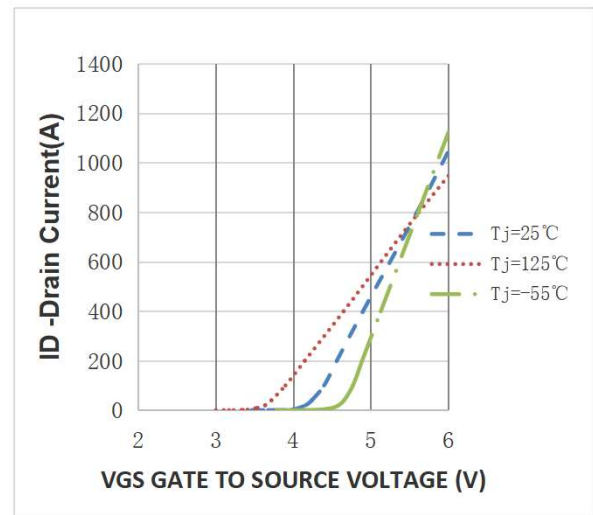


Fig.11 Safe Operating Area

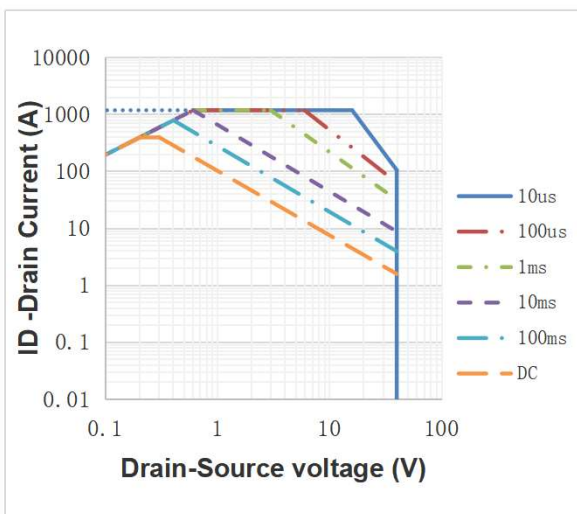
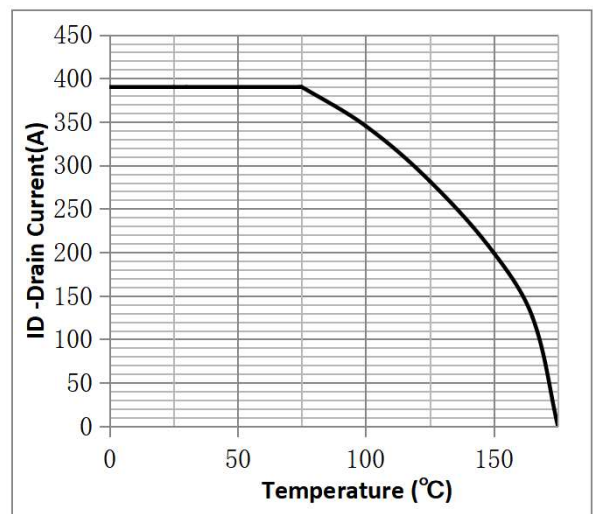
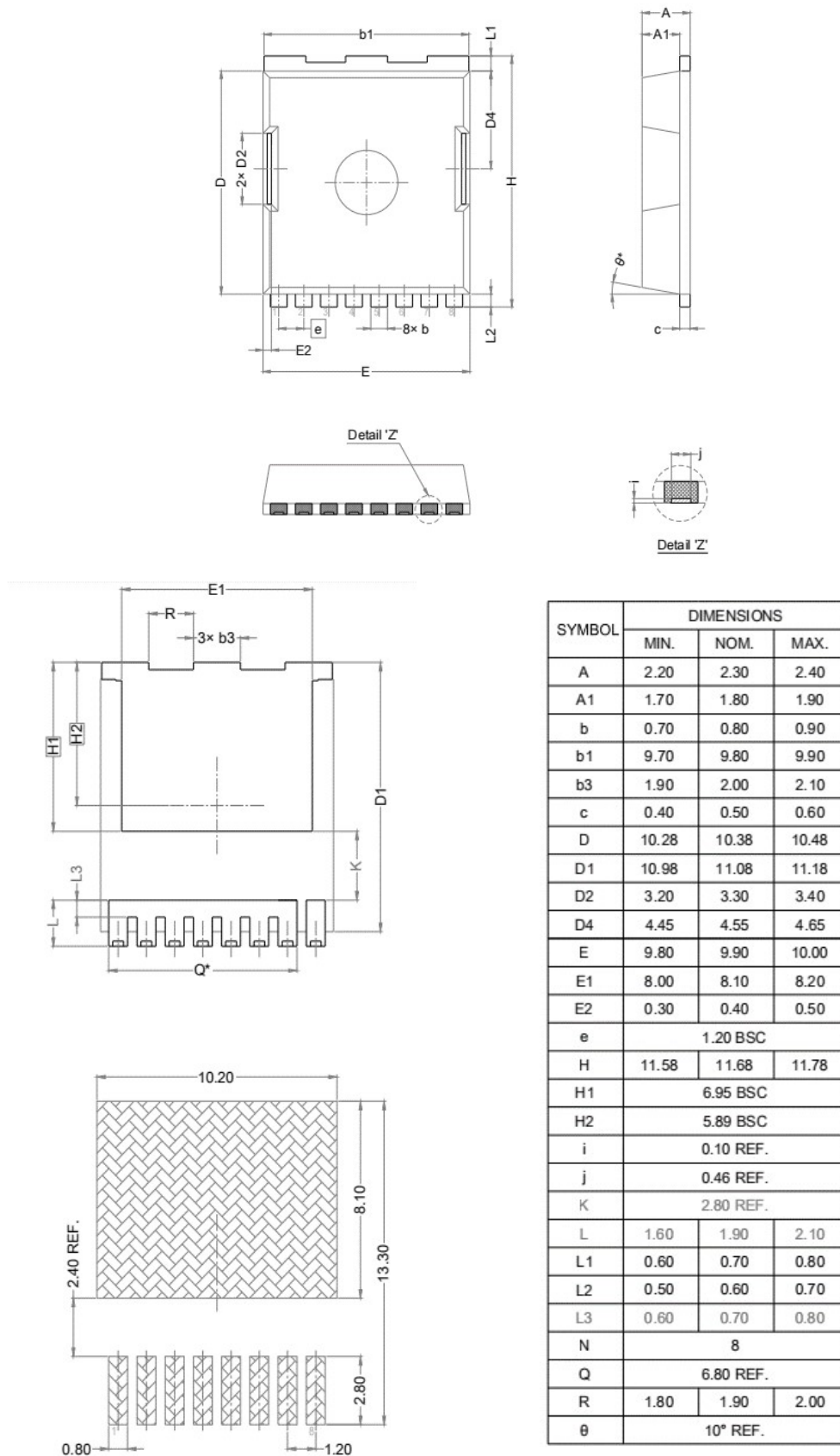


Fig.12 I_D vs. Junction Temperature^③



•TOLL Package Outline



Note:

- ① Pulse : $V_{GS}=+20V/-20V$, Duty cycle=50%, $T_j=175^{\circ}C$, $t=1000$ hours; For DC , the following test conditions can be passed: $V_{GS}=+20V/-10V$, $T_j=175^{\circ}C$, $t=1000$ hours;
- ② Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate;
- ③ Practically the current will be limited by PCB, thermal design and operating temperature. $V_{GS}=10V$.

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Revision History

Version	Date	Change
A	2022.1.15	new
B	2022.9.10	1.Add Reach,HF figure 2.ID curve modify
C	2023.1.6	1.Correct Dynamic characteristics 2.correct symbol figure 3.modified ID,EAS
C1	2023.3.30	Correct marking mistake
D	2023.12.18	Correct SOA
E	2024.11.6	RDSon modified.